



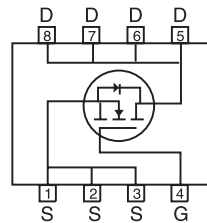
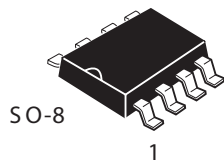
N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
60V	15A	10 @ V _{GS} =10V
		13.5 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V _{DS}	Drain-Source Voltage		60	V
V _{GS}	Gate-Source Voltage		±20	V
I _D	Drain Current-Continuous ^c	T _C =25°C	15	A
		T _C =70°C	12	A
I _{DM}	-Pulsed ^{a c}		75	A
E _{AS}	Single Pulse Avalanche Energy ^d		225	mJ
P _D	Maximum Power Dissipation	T _C =25°C	2.5	W
		T _C =70°C	1.6	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient	50	°C/W
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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.6	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =7.5A		8	10	m ohm
		V _{GS} =4.5V , I _D =6.5A		11	13.5	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =7.5A		21		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =25V,V _{GS} =0V f=1.0MHz		4250		pF
C _{OSS}	Output Capacitance			247		pF
C _{RSS}	Reverse Transfer Capacitance			216		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =30V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		57		ns
t _r	Rise Time			61		ns
t _{D(OFF)}	Turn-Off Delay Time			173		ns
t _f	Fall Time			50		ns
Q _g	Total Gate Charge	V _{DS} =30V,I _D =7.5A,V _{GS} =10V		55		nC
		V _{DS} =30V,I _D =7.5A,V _{GS} =4.5V		26		nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V,I _D =7.5A,		4.5		nC
Q _{gd}	Gate-Drain Charge	V _{GS} =10V		14		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =3A		0.76	1.3	V

Notes

- Pulse Test: Pulse Width ≤ 10us, Duty Cycle ≤ 1%.
- Guaranteed by design, not subject to production testing.
- Drain current limited by maximum junction temperature.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 30V. (See Figure13)
- Mounted on FR4 Board of 1 inch², 2oz.

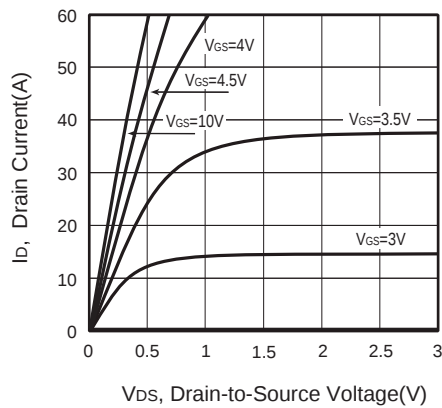


Figure 1. Output Characteristics

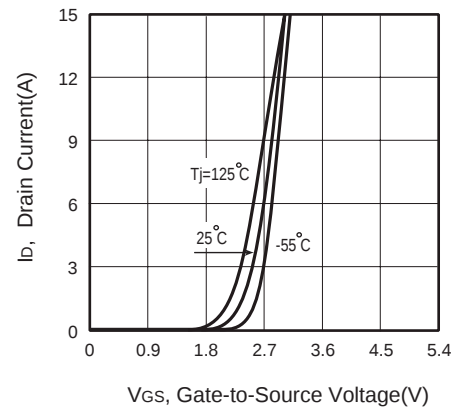


Figure 2. Transfer Characteristics

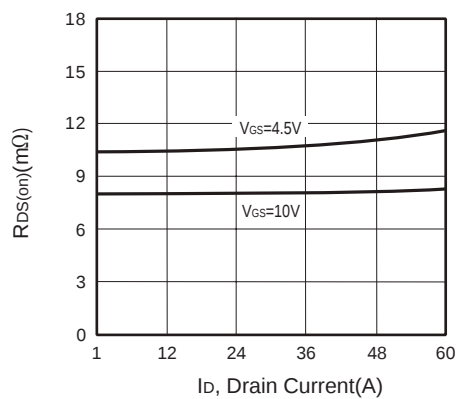


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

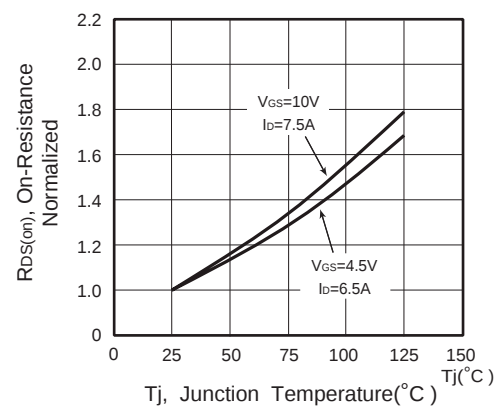


Figure 4. On-Resistance Variation with Drain Current and Temperature

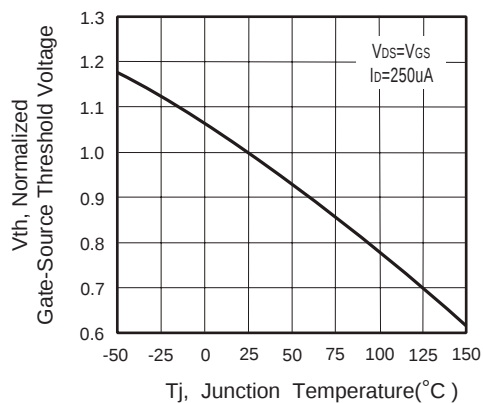


Figure 5. Gate Threshold Variation with Temperature

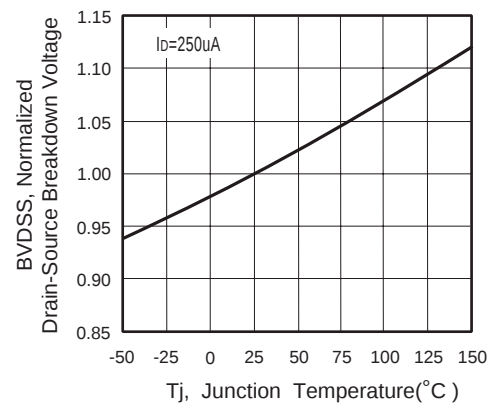


Figure 6. Breakdown Voltage Variation with Temperature

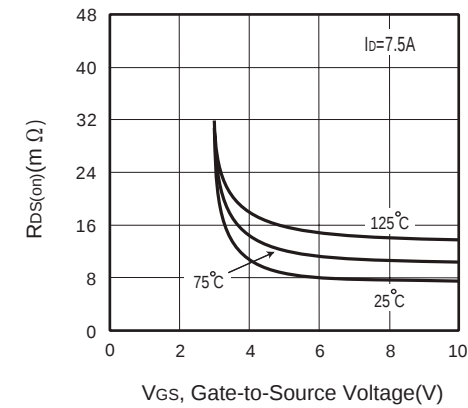


Figure 7. On-Resistance vs. Gate-Source Voltage

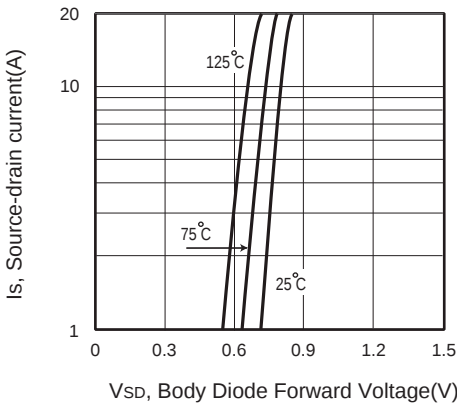


Figure 8. Body Diode Forward Voltage Variation with Source Current

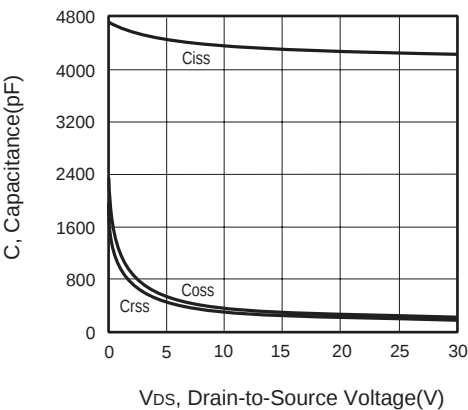


Figure 9. Capacitance

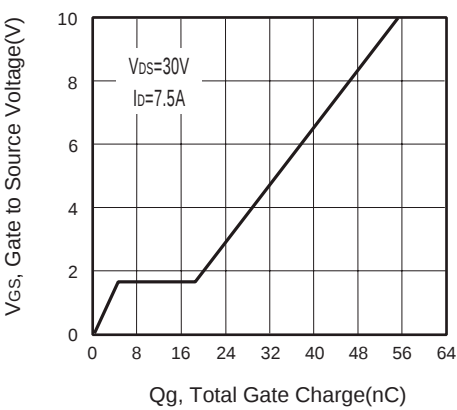


Figure 10. Gate Charge

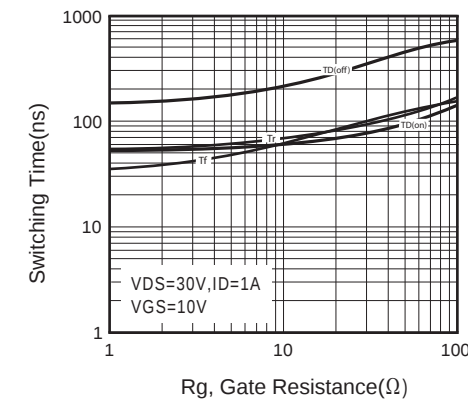


Figure 11. switching characteristics

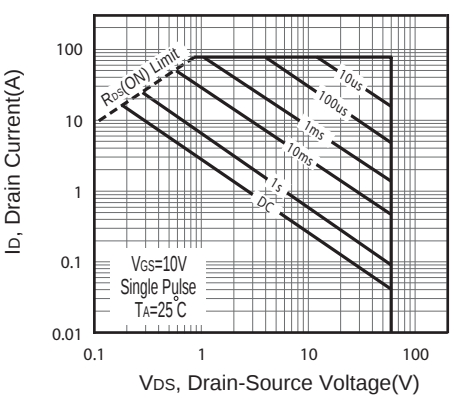
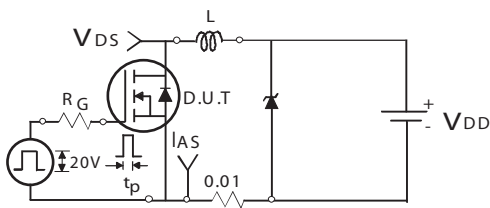
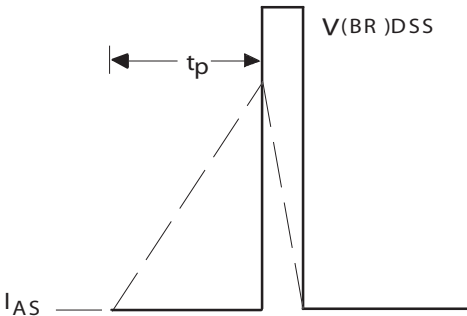


Figure 12. Maximum Safe Operating Area



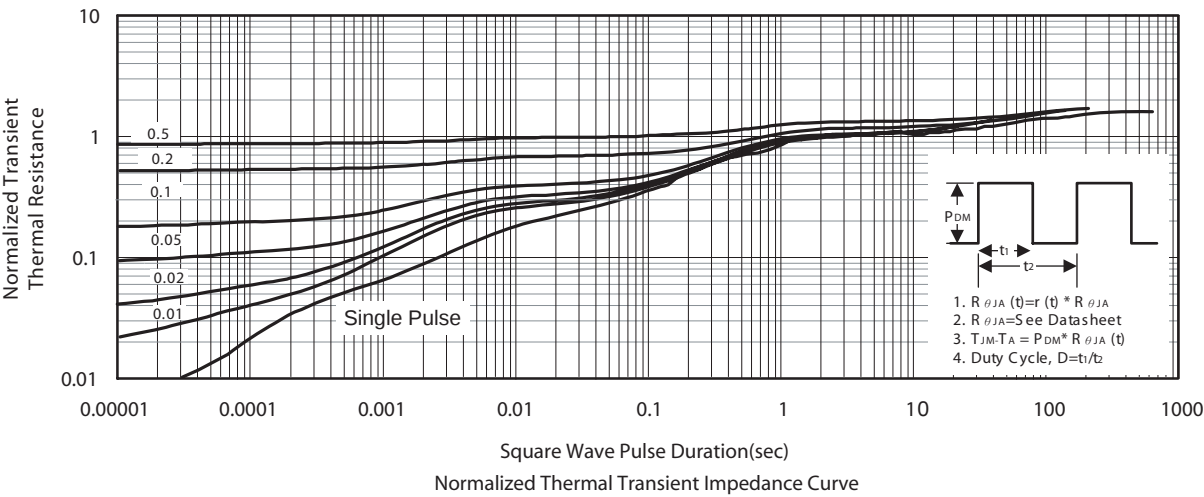
Unclamped Inductive Test Circuit

Figure 13a.



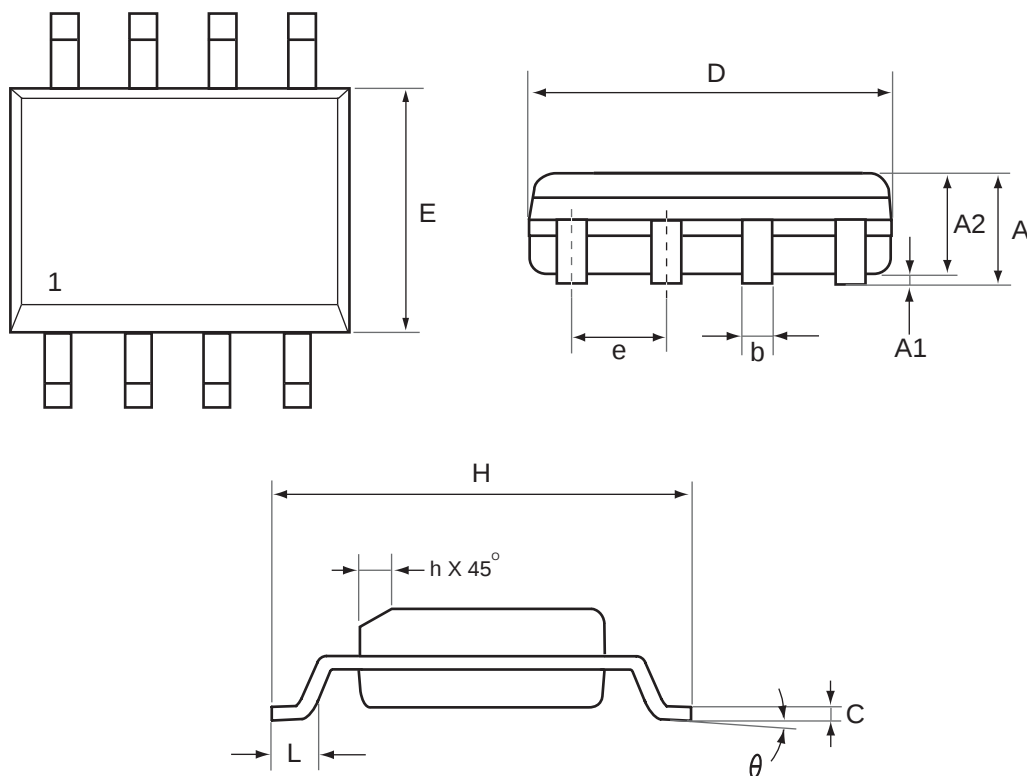
Unclamped Inductive Waveforms

Figure 13b.



PACKAGE OUTLINE DIMENSIONS

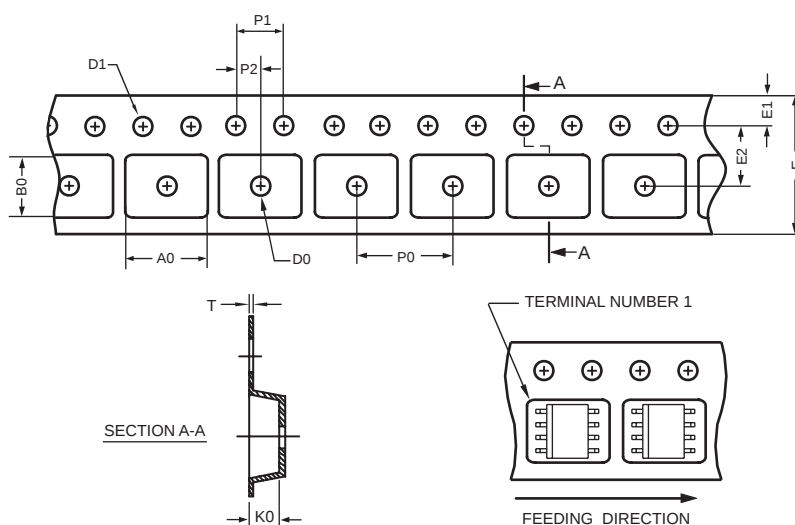
SO-8



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	1.63	0.049	0.064
b	0.31	0.51	0.012	0.020
C	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	3.70	4.00	0.146	0.157
e	1.27 REF.		0.050 BSC	
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°
h	0.25	0.50	0.010	0.020

SO-8 Tape and Reel Data

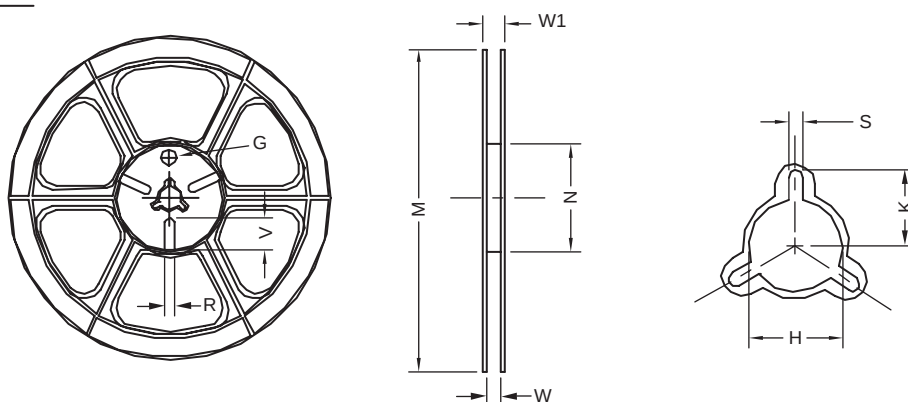
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.50 ±0.15	5.25 ±0.10	2.10 ±0.10	φ 1.5 (MIN)	φ 1.55 ±0.10	12.0 +0.3 - 0.1	1.75 ±0.10	5.5 ±0.10	8.0 ±0.10	4.0 ±0.10	2.0 ±0.10	0.30 ±0.013

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	φ 330	330 ± 1	62 ±1.5	12.4 + 0.2	16.8 - 0.4	φ 12.75 + 0.15	---	2.0 ±0.15	---	---	---

TOP MARKING DEFINITION

SO-8

